

PHP28NQ15T

N-channel TrenchMOS standard level FET

Rev. 02 — 22 March 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Increased efficiency during switching due to low body diode recovered charge
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- Class-D audio amplifiers
- DC-to-AC inverters

- DC-to-DC convertors
- Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	150	٧
I _D	drain current	$T_j = 25$ °C; $V_{GS} = 10$ V; see Figure 1 and 3	-	-	28.5	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	150	W
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 75 \text{ V}; T_j = 25 \text{ °C};$ see Figure 12 and 11	-	7.5	-	nC
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 18 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{Model}} \text{ and } \frac{10}{\text{Model}}$	-	54	65	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow A$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHP28NQ15T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

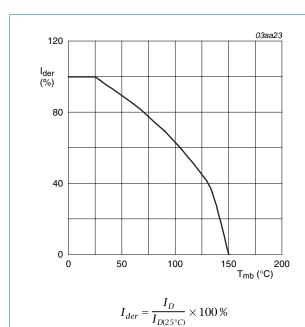
4. Limiting values

Table 4. Limiting values

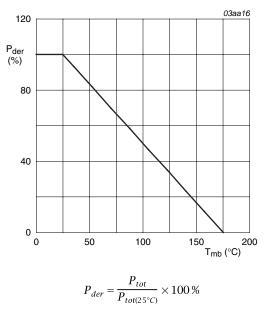
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	150	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	150	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{A}} \text{ and } \frac{3}{\text{C}}$	-	28.5	Α
		$V_{GS} = 10 \text{ V}; T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	20.2	Α
I _{DM}	peak drain current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 3}}{}$	-	57.1	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
Is	source current	$T_{mb} = 25 ^{\circ}C$	-	28.5	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	57.1	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 9.9 A; $V_{sup} \le$ 150 V; R_{GS} = 50 Ω ; t_p = 0.1 ms; unclamped	-	100	mJ

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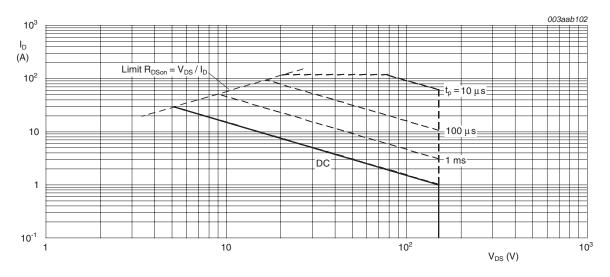


Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Normalized total power dissipation as a Fig 2. function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = -10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

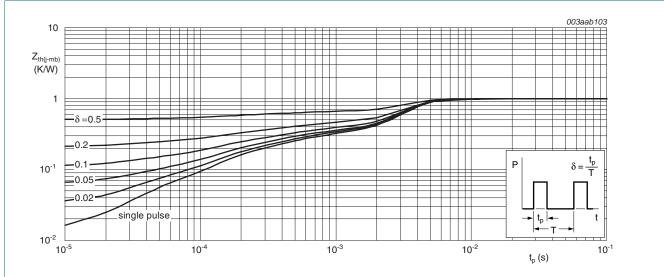


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	135	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	150	-	-	V
V _{GS(th)} gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 7</u> and <u>8</u>	-	-	4.4	V	
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 7</u> and <u>8</u>	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 7</u> and <u>8</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 120 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 120 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nΑ
R _{DSon} drain-source on-state resistance	V_{GS} = 10 V; I_D = 18 A; T_j = 175 °C; see <u>Figure 9</u> and <u>10</u>	-	145	175	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 18 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{see } \frac{\text{Figure 9}}{\text{and } \frac{10}{\text{C}}}$	-	54	65	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz; T _j = 25 °C	-	1.1	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 75 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 11 and 12	-	24	-	nC
Q_{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 75 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C};$	-	6	-	nC
Q_{GD}	gate-drain charge	see Figure 12 and 11	-	7.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 75 V; T_j = 25 °C; see <u>Figure 11</u> and <u>12</u>	-	5	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	1250	-	pF
C _{oss}	output capacitance	see <u>Figure 13</u>	-	185	-	pF
C_{rss}	reverse transfer capacitance		-	55	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 75 \text{ V}; R_L = 3 \Omega; V_{GS} = 10 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	20	-	ns
t _{d(off)}	turn-off delay time	V_{DS} = 75 V; R_L = 3 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ 5.6 Ω ; T_j = 25 °C	-	12	-	ns
t _f	fall time	$V_{DS} = 75 \text{ V}; R_L = 3 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}\text{C}$	-	55	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 14	-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	110	-	ns
Qr	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	170	-	nC

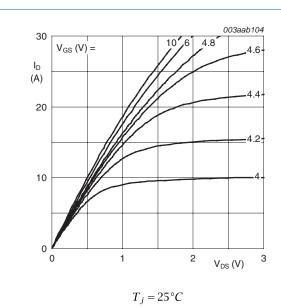
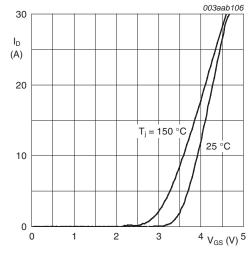
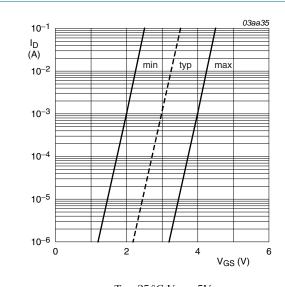


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



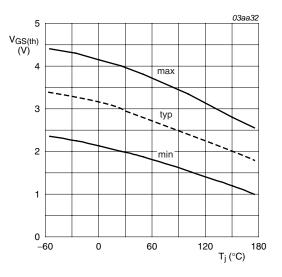
 $T_j = 25$ °C and 150°C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \, mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature

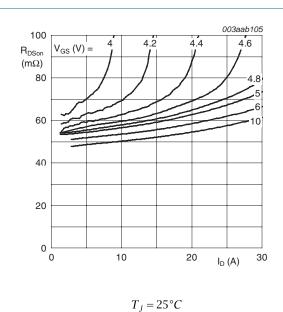


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

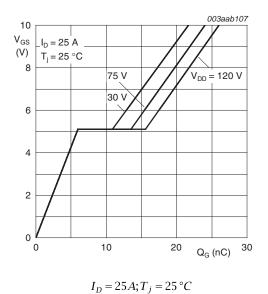


Fig 11. Gate-source voltage as a function of gate charge; typical values

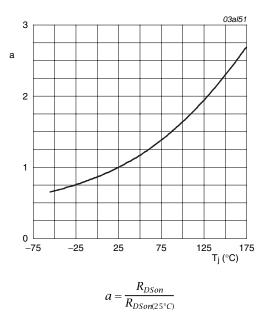


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

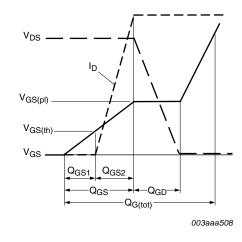


Fig 12. Gate charge waveform definitions

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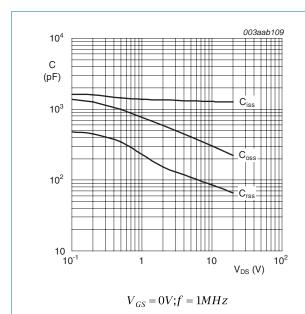


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

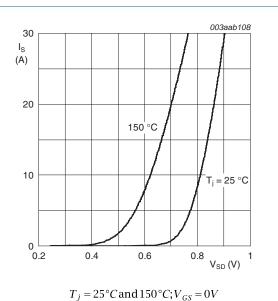
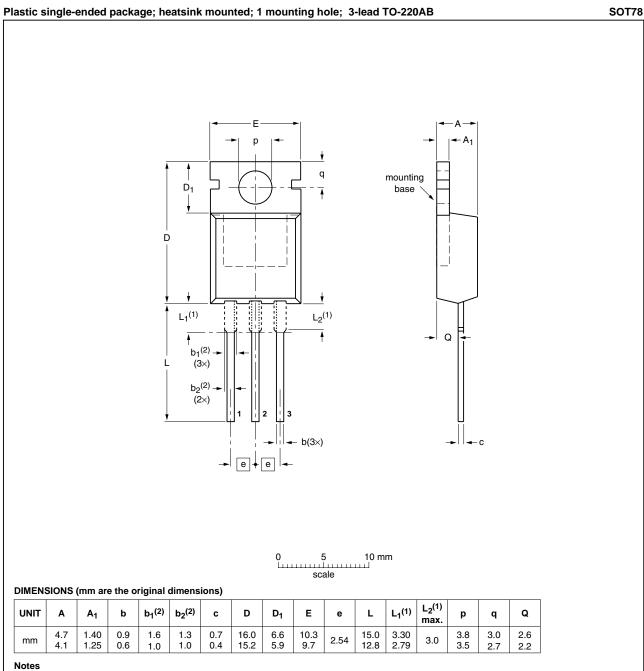


Fig 14. Source current as a function of source-drain voltage; typical values

Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC JEDEC JEITA		JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 15. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP28NQ15T_2	20100322	Product data sheet	-	PHP28NQ15T_1
Modifications:		of this data sheet has beer of NXP Semiconductors.	n redesigned to comply w	ith the new identity
	 Legal texts 	have been adapted to the	new company name whe	re appropriate.
PHP28NQ15T_1	20050817	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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